

A 125MHz Burst Mode 0.18 μ m 128Mbit 2 Bits per Cell Flash Memory

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We describe the design of a high performance 2 bits per cell Flash memory device capable of 8ns synchronous access rate capable of operation at up to 125MHz in burst mode and asynchronous page mode access rate of 14ns. The device is fabricated on Intel's 0.18 μ m ETOX™ VII Process technology.